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PTO/SB/08A (08-00)

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Substitute for form 1449A/PTO INFORMATION DISCLOSURE STATEMENT BY APPLICANT <i>(use as many sheets as necessary)</i>				Complete If Known	
Application Number		10/765 292			
Filing Date		27 January 2004 (herewith)			
First Named Inventor		Tzu-Hsuan Hsu et al.			
Group Art Unit		2827			
Examiner Name		M. TRAN			
Attorney Docket Number		MXIC 1561-1			
Sheet	1	of	2		

U.S. PATENT DOCUMENTS						
Examiner Initials*	Cite No. ¹	U.S. Patent Document		Name of Patentee or Applicant of Cited Document	Date of Publication of Cited Document MM-DD-YYYY	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear
		Number	Kind Code ² (if known)			
MT	A1	5,768,192		Eitan	06-16-1998	
↑	A2	5,966,603		Eitan	10-12-1999	
	A3	6,011,725		Eitan	01-04-2000	
	A4	6,074,917		Chang et al.	06-13-2000	
	A5	6,219,276		Parker	04-17-2001	
	A6	6,297,096		Boaz	10-02-2001	
	A7	6,320,786		Chang et al.	11-20-2001	
	A8	6,396,741		Bloom et al.	05-28-2002	
MT	A9	6,487,114		Jong et al.	11-26-2002	
	A10					
	A11					
	A12					
	A13					
	A14					
	A15					
	A16					
	A17					
	A18					
	A19					
	A20					

FOREIGN PATENT DOCUMENTS								
Examiner Initials ¹	Cite No. ¹	Foreign Patent Document			Name of Patentee or Applicant of Cited Document	Date of Publication of Cited Document MM-DD-YYYY	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear	To
		Office ³	Number ⁴	Kind Code ⁵ (if known)				
	B1							
	B2							
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	B6							
	B7							
	B8							
	B9							
	B10							

Examiner Signature	M. TRAN	Date Considered	3/18/05
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¹ Unique citation designation number. ² See attached Kinds of U.S. Patent Documents. ³ Enter Office that issued the document, by the two-letter code (WIPO Standard ST.3). ⁴ For Japanese patent documents, the indication of the year of the reign of the Emperor must precede the serial number of the patent document. ⁵ Kind of document by the appropriate symbols as indicated on the document under WIPO Standard ST. 16 if possible. ⁶ Applicant is to place a check mark here if English language Translation is attached.

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Substitute for form 1449B/PTO		C mplete if Known	
INFORMATION DISCLOSURE STATEMENT BY APPLICANT (use as many sheets as necessary)		Application Number	10/ 765 292
		Filing Date	27 January 2004 (herewith)
		First Named Inventor	Tzu-Hsuan Hsu et al.
		Group Art Unit	2827
		Examiner Name	M. TRAN
		Attorney Docket Number	MXIC 1561-1
Sheet	2	of	2

OTHER PRIOR ART – NON PATENT LITERATURE DOCUMENTS			
Examiner Initials*	Cite No. ¹	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-issue number(s), publisher, city and/or country where published.	T ²
MT	C1	LUSKY, ELI, et al., "Spatial Characterization of Channel hot electron injection Utilizing subthreshold slope of the localized charge storage NROM memory device," Non-Volatile Semiconductor Memory Workshop, Monterey, CA (Aug 2001), 2 pages	
1	C2	LUSKY, ELI, et al., "Electron Discharge Model of Locally-Trapped Charge in Oxide-Nitride-Oxide (ONO) Gates for NROM Non-Volatile Semiconductor Memory Device," SSDM, Tokyo, Japan (Sep 2001), 2 pages.	
MT	C3	BOAZ, EITAN, et al, "Can NROM, a 2-bit, Trapping Storage NVM Cell, Give a Real Challenge to Floating Gate Cells?" SSDM, Tokyo, Japan (1999).	

Examiner Signature	M. TRAN	Date Considered	3/18/05
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